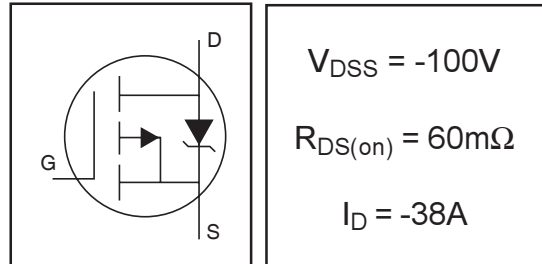


IRF5210SPbF
IRF5210LPbF

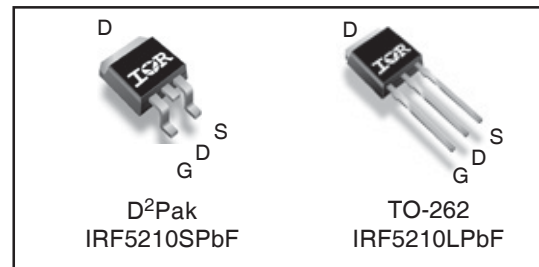
HEXFET® Power MOSFET

- Advanced Process Technology
- Ultra Low On-Resistance
- 150°C Operating Temperature
- Fast Switching
- Repetitive Avalanche Allowed up to T_{jmax}
- Some Parameters are Different from IRF5210S/L
- P-Channel
- Lead-Free



Description

Features of this design are a 150°C junction operating temperature, fast switching speed and improved repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in a wide variety of other applications.



| | | |
|----------|----------|----------|
| G | D | S |
| Gate | Drain | Source |

Absolute Maximum Ratings

| | Parameter | Max. | Units |
|---------------------------|---|------------------------|-------|
| $I_D @ T_C = 25^\circ C$ | Continuous Drain Current, $V_{GS} @ -10V$ | -38 | A |
| $I_D @ T_C = 100^\circ C$ | Continuous Drain Current, $V_{GS} @ -10V$ | -24 | |
| I_{DM} | Pulsed Drain Current ① | -140 | |
| $P_D @ T_A = 25^\circ C$ | Maximum Power Dissipation | 3.1 | W |
| $P_D @ T_C = 25^\circ C$ | Maximum Power Dissipation | 170 | |
| | Linear Derating Factor | 1.3 | W/°C |
| V_{GS} | Gate-to-Source Voltage | ± 20 | V |
| E_{AS} | Single Pulse Avalanche Energy ② | 120 | mJ |
| I_{AR} | Avalanche Current ① | -23 | A |
| E_{AR} | Repetitive Avalanche Energy ① | 17 | mJ |
| dv/dt | Peak Diode Recovery dv/dt ③ | -7.4 | V/ns |
| T_J | Operating Junction and | -55 to + 150 | °C |
| T_{STG} | Storage Temperature Range | | |
| | Soldering Temperature, for 10 seconds | 300 (1.6mm from case) | |

Thermal Resistance

| | Parameter | Typ. | Max. | Units |
|-----------------|---|------|------|-------|
| $R_{\theta JC}$ | Junction-to-Case | — | 0.75 | °C/W |
| $R_{\theta JA}$ | Junction-to-Ambient (PCB Mount, steady state) ⑤ | — | 40 | |

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|------------------------------|--------------------------------------|------|-------|------|------------|--|
| $V_{(BR)DSS}$ | Drain-to-Source Breakdown Voltage | -100 | — | — | V | $V_{GS} = 0V, I_D = -250\mu A$ |
| $\Delta BV_{DSS}/\Delta T_J$ | Breakdown Voltage Temp. Coefficient | — | -0.11 | — | V/°C | Reference to $25^\circ\text{C}, I_D = -1\text{mA}$ |
| $R_{DS(on)}$ | Static Drain-to-Source On-Resistance | — | — | 60 | m Ω | $V_{GS} = 10V, I_D = -38A$ ④ |
| $V_{GS(th)}$ | Gate Threshold Voltage | -2.0 | — | -4.0 | V | $V_{DS} = V_{GS}, I_D = -250\mu A$ |
| gfs | Forward Transconductance | 9.5 | — | — | S | $V_{DS} = -50V, I_D = -23A$ |
| I_{DSS} | Drain-to-Source Leakage Current | — | — | -50 | μA | $V_{DS} = -100V, V_{GS} = 0V$ $V_{DS} = -80V, V_{GS} = 0V, T_J = 125^\circ\text{C}$ |
| I_{GSS} | Gate-to-Source Forward Leakage | — | — | 100 | nA | $V_{GS} = 20V$ |
| | Gate-to-Source Reverse Leakage | — | — | -100 | nA | $V_{GS} = -20V$ |
| Q_g | Total Gate Charge | — | 150 | 230 | nC | $I_D = -23A$ |
| Q_{gs} | Gate-to-Source Charge | — | 22 | 33 | nC | $V_{DS} = -80V$ |
| Q_{gd} | Gate-to-Drain ("Miller") Charge | — | 81 | 120 | nC | $V_{GS} = -10V$ ④ |
| $t_{d(on)}$ | Turn-On Delay Time | — | 14 | — | ns | $V_{DD} = -50V$ |
| t_r | Rise Time | — | 63 | — | ns | $I_D = -23A$ |
| $t_{d(off)}$ | Turn-Off Delay Time | — | 72 | — | ns | $R_G = 2.4\Omega$ |
| t_f | Fall Time | — | 55 | — | ns | $V_{GS} = -10V$ ④ |
| L_D | Internal Drain Inductance | — | 4.5 | — | nH | Between lead, 6mm (0.25in.) from package and center of die contact |
| L_S | Internal Source Inductance | — | 7.5 | — | nH | |
| C_{iss} | Input Capacitance | — | 2780 | — | pF | $V_{GS} = 0V$ |
| C_{oss} | Output Capacitance | — | 800 | — | pF | $V_{DS} = -25V$ |
| C_{rss} | Reverse Transfer Capacitance | — | 430 | — | pF | $f = 1.0\text{MHz}$, See Fig. 5 |

Source-Drain Ratings and Characteristics

| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|----------|---|---|------|------|-------|---|
| I_S | Continuous Source Current (Body Diode) | — | — | -38 | A | MOSFET symbol showing the integral reverse p-n junction diode. |
| I_{SM} | Pulsed Source Current (Body Diode) ① | — | — | -140 | A | |
| V_{SD} | Diode Forward Voltage | — | — | -1.6 | V | $T_J = 25^\circ\text{C}, I_S = -23A, V_{GS} = 0V$ ④ |
| t_{rr} | Reverse Recovery Time | — | 170 | 260 | ns | $T_J = 25^\circ\text{C}, I_F = -23A, V_{DD} = -25V$ |
| Q_{rr} | Reverse Recovery Charge | — | 1180 | 1770 | nC | $di/dt = -100A/\mu s$ ④ |
| t_{on} | Forward Turn-On Time | Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D) | | | | |

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ② Starting $T_J = 25^\circ\text{C}$, $L = 0.46\text{mH}$
 $R_G = 25\Omega, I_{AS} = -23A$. (See Figure 12)
- ③ $I_{SD} \leq -23A, di/dt \leq -650A/\mu s, V_{DD} \leq V_{(BR)DSS}, T_J \leq 150^\circ\text{C}$.

- ④ Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.
- ⑤ When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994.

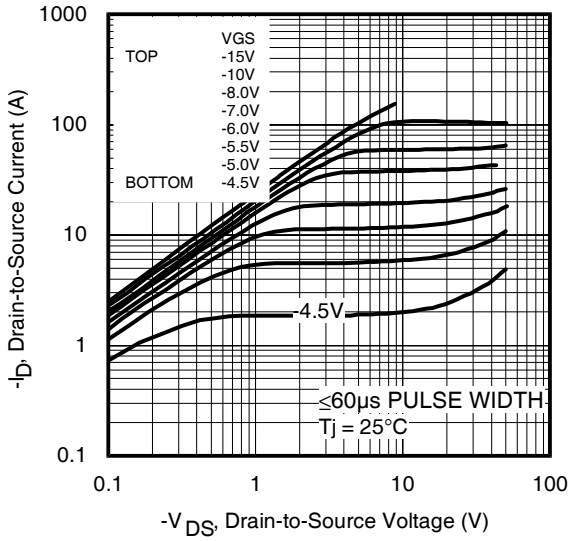


Fig 1. Typical Output Characteristics

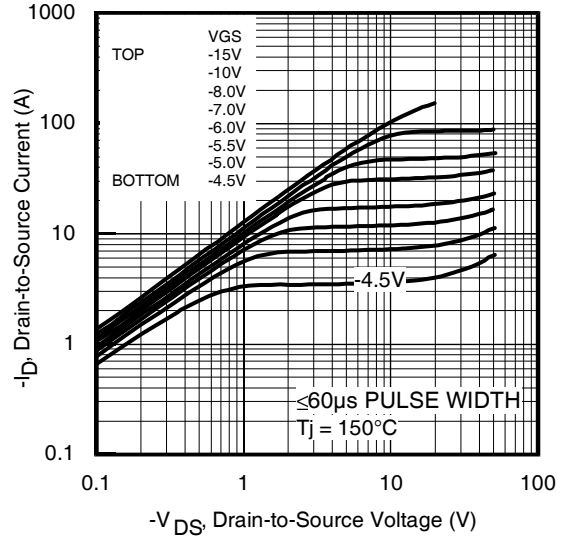


Fig 2. Typical Output Characteristics

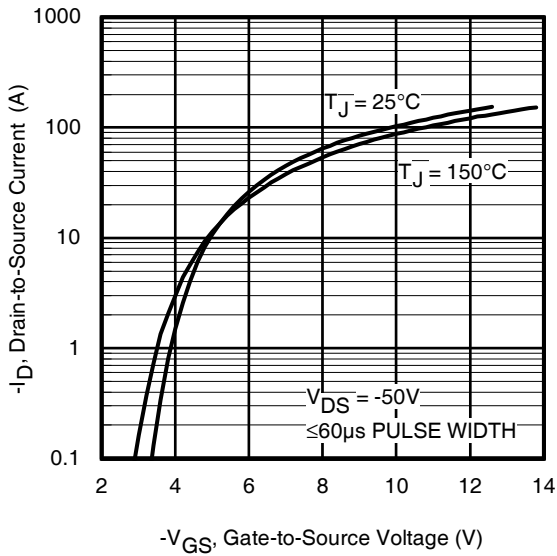


Fig 3. Typical Transfer Characteristics

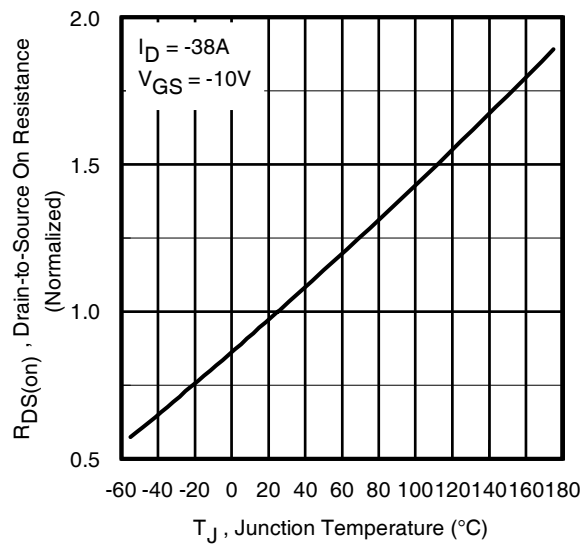


Fig 4. Normalized On-Resistance vs. Temperature

IRF5210S/LPbF

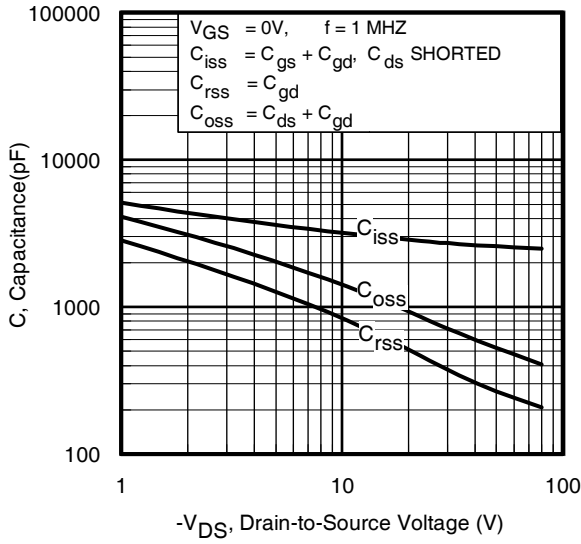


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

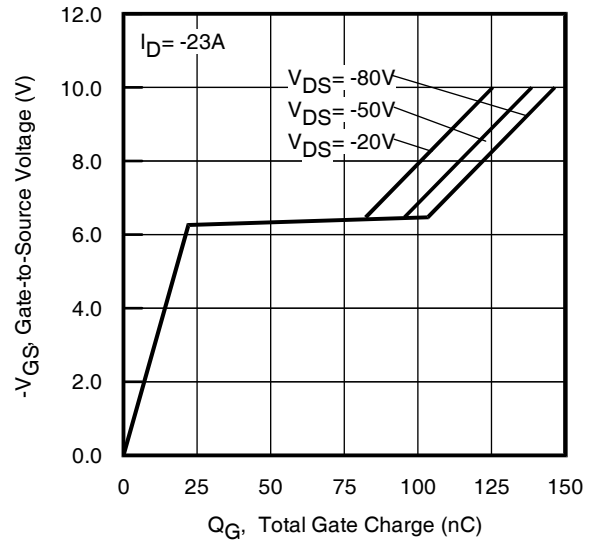


Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage

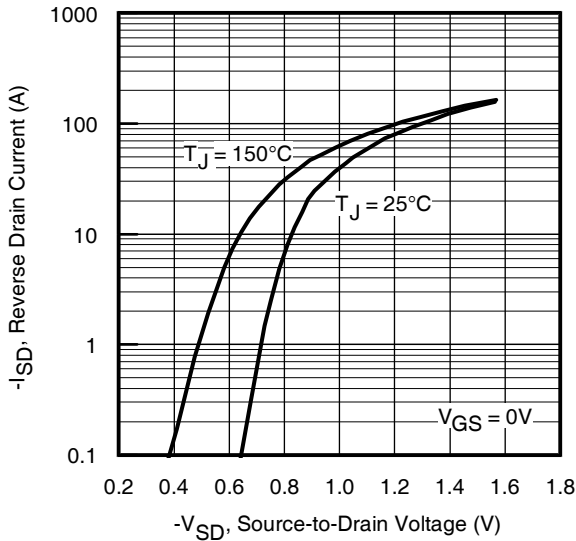


Fig 7. Typical Source-Drain Diode Forward Voltage

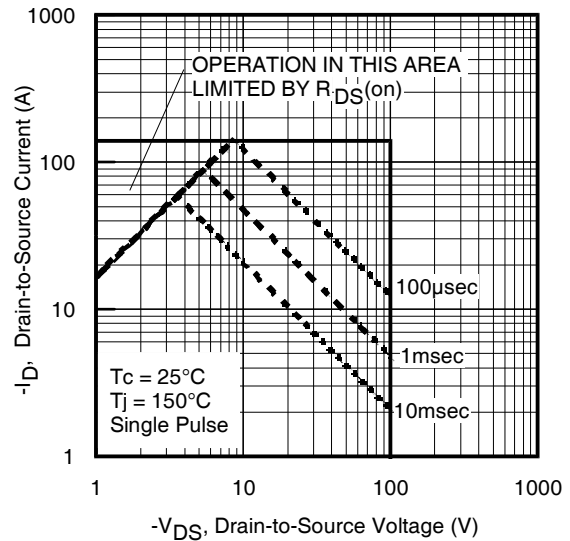


Fig 8. Maximum Safe Operating Area

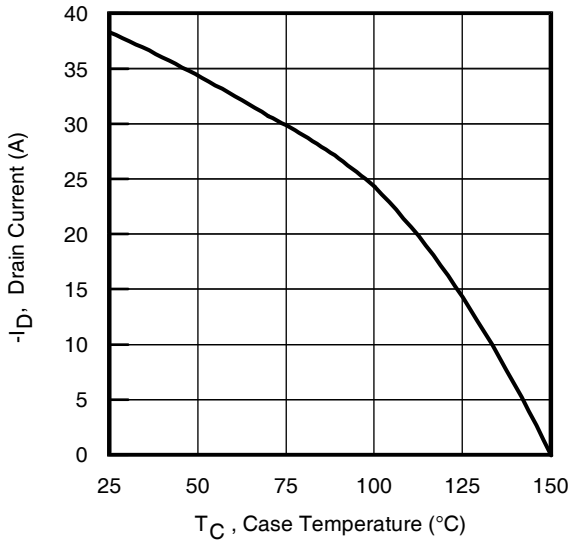


Fig 9. Maximum Drain Current vs. Case Temperature

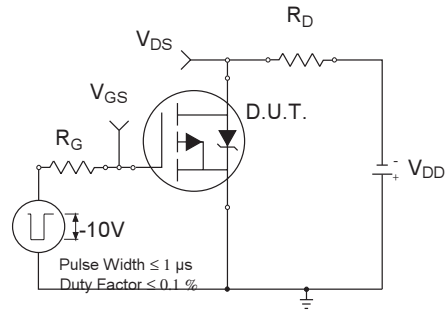


Fig 10a. Switching Time Test Circuit

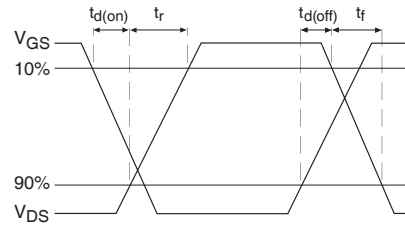


Fig 10b. Switching Time Waveforms

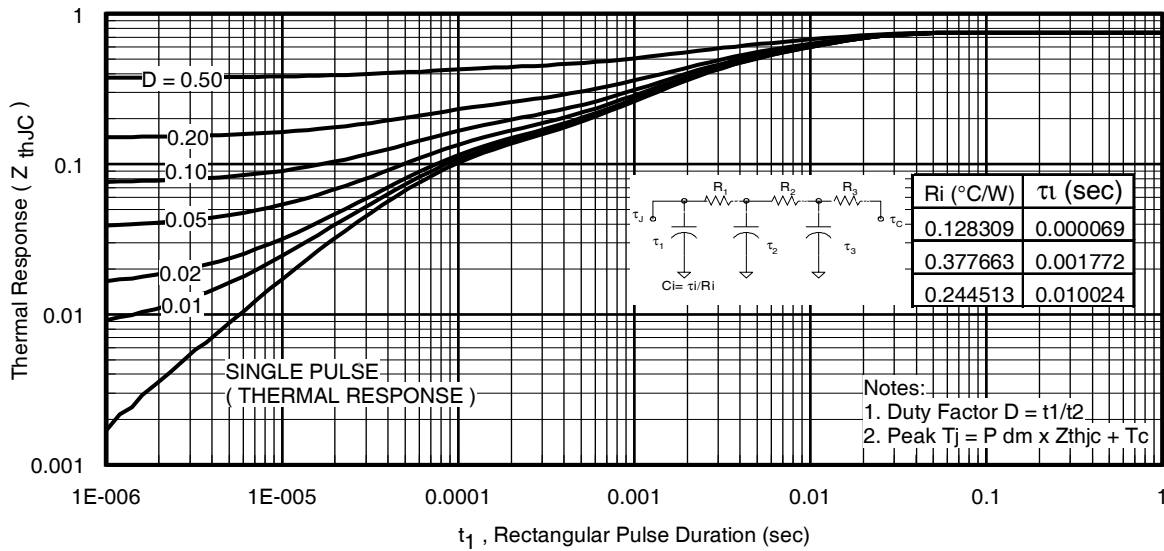


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

IRF5210S/LPbF

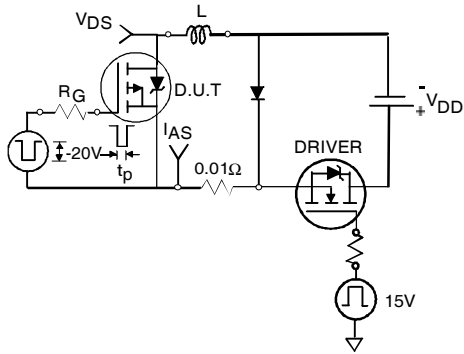


Fig 12a. Unclamped Inductive Test Circuit

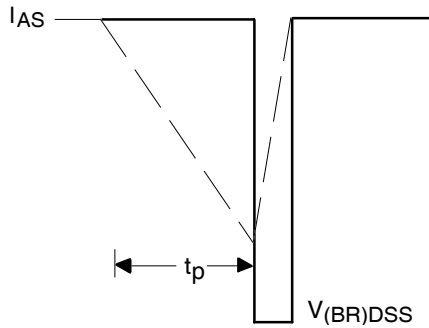


Fig 12b. Unclamped Inductive Waveforms

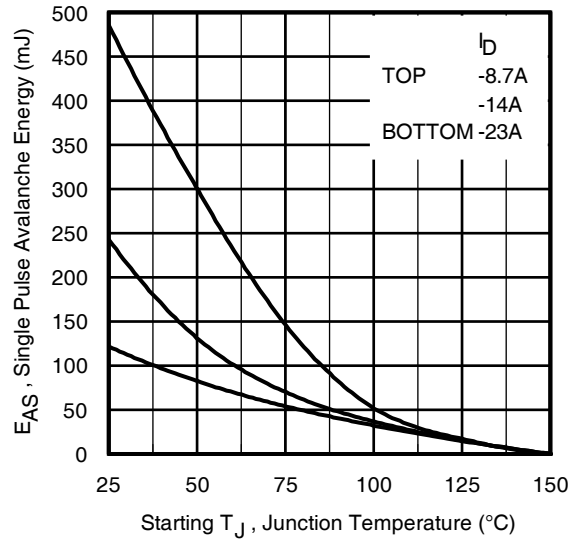


Fig 13. Maximum Avalanche Energy vs. Drain Current

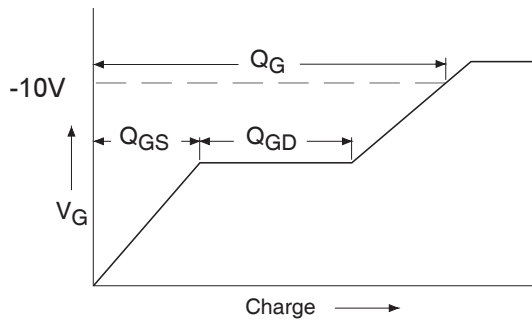


Fig 14a. Basic Gate Charge Waveform

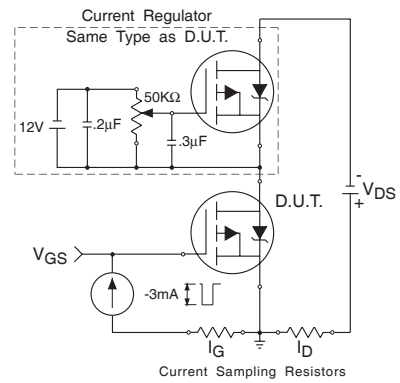
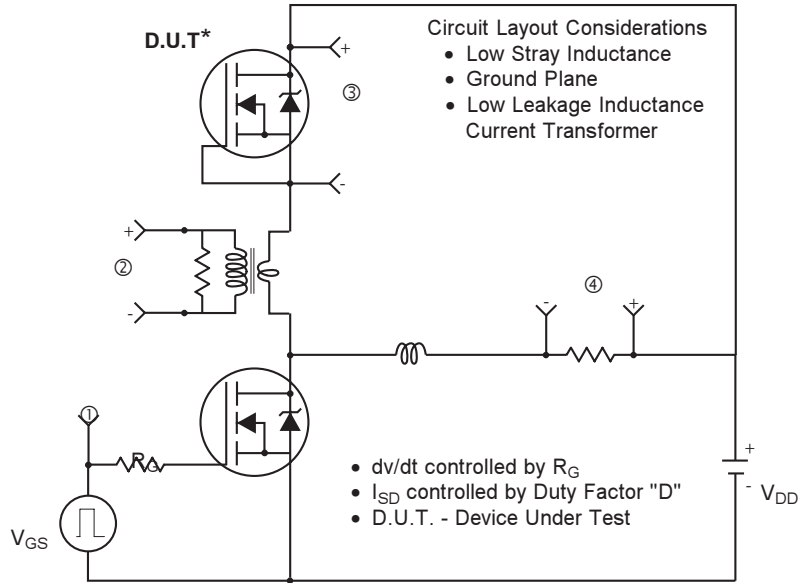
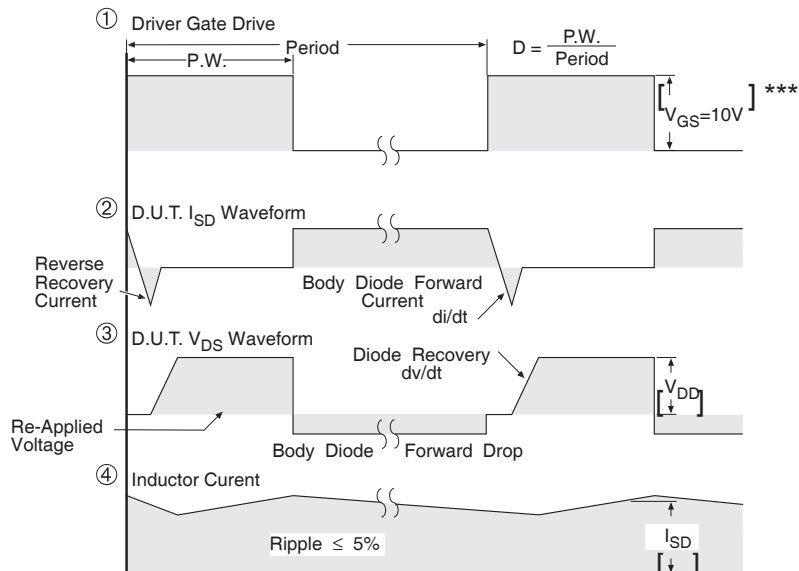


Fig 14b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit



* Reverse Polarity of D.U.T for P-Channel



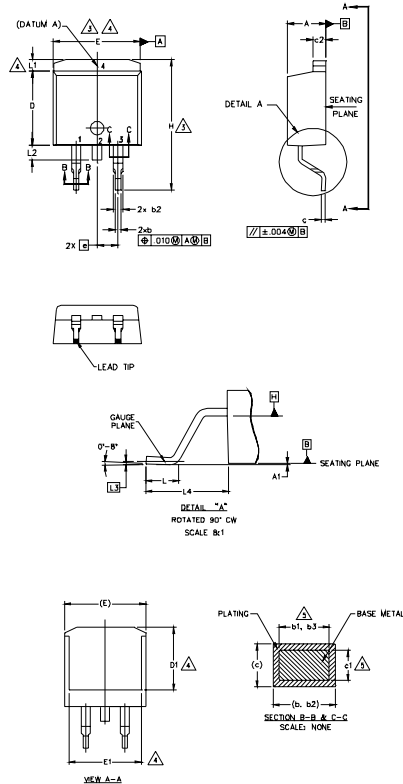
*** $V_{GS} = 5.0V$ for Logic Level and 3V Drive Devices

Fig 15. For P-Channel HEXFETS

IRF5210S/LPbF

D²Pak (TO-263AB) Package Outline

Dimensions are shown in millimeters (inches)



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
 2. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES)
 3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [0.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY AT DATUM H.
 4. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSION E, L1, D1 & E1.
 5. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
 6. DATUM A & B TO BE DETERMINED AT DATUM PLANE H.
 7. CONTROLLING DIMENSION: INCH.
 8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-263AB.

| SYMBOL | DIMENSIONS | | | | NOTES |
|--------|-------------|-------|----------|------|-------|
| | MILLIMETERS | | INCHES | | |
| A | 4.06 | 4.83 | .160 | .190 | |
| A1 | 0.00 | 0.254 | .000 | .010 | |
| b | 0.51 | 0.99 | .020 | .039 | |
| b1 | 0.51 | 0.89 | .020 | 0.35 | 5 |
| b2 | 1.14 | 1.78 | .045 | .070 | |
| b3 | 1.14 | 1.73 | .045 | .068 | 6 |
| c | 0.38 | 0.74 | .015 | .029 | |
| c1 | 0.38 | 0.58 | .015 | 0.23 | 5 |
| c2 | 1.14 | 1.65 | .045 | .065 | |
| D | 8.36 | 9.65 | .330 | .380 | 3 |
| D1 | 6.86 | - | .270 | - | 4 |
| E | 9.65 | 10.67 | .380 | .420 | 3,4 |
| E1 | 6.22 | - | .245 | - | 4 |
| e | 2.54 BSC | | .100 BSC | | |
| H | 14.61 | 15.08 | .575 | .625 | |
| L | 1.78 | 2.79 | .070 | .110 | |
| L1 | - | 1.65 | - | .066 | 4 |
| L2 | 1.27 | 1.78 | - | .070 | |
| L3 | 0.25 BSC | | .010 BSC | | |
| L4 | 4.78 | 5.28 | .188 | .208 | |

LEAD ASSIGNMENTS

- HEXFET
- 1.- GATE
 - 2, 4.- DRAIN
 - 3.- SOURCE

IGBTs, COPACK

- 1.- GATE
- 2, 4.- COLLECTOR
- 3.- EMITTER

DIODES

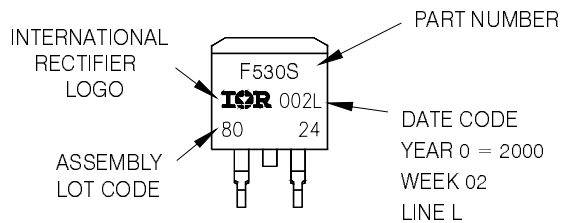
- 1.- ANODE *
- 2, 4.- CATHODE
- 3.- ANODE

* PART DEPENDENT.

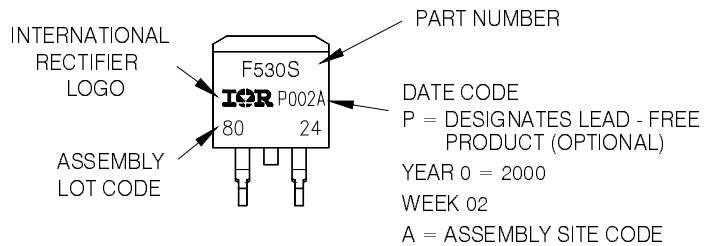
D²Pak (TO-263AB) Part Marking Information

EXAMPLE: THIS IS AN IRF530S WITH
LOT CODE 8024
ASSEMBLED ON WW 02, 2000
IN THE ASSEMBLY LINE "L"

Note: "P" in assembly line position indicates "Lead - Free"



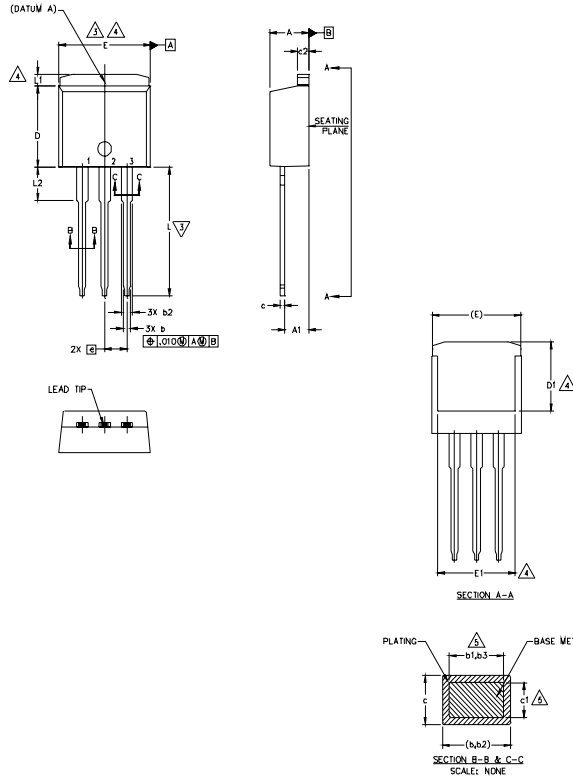
OR



Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

TO-262 Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [0.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
4. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSION E, L1, D1 & E1.
5. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
6. CONTROLLING DIMENSION: INCH.
7. OUTLINE CONFORM TO JEDEC TO-262 EXCEPT A1(max.), b(min.), AND D1(min.) WHERE DIMENSIONS DERIVED THE ACTUAL PACKAGE OUTLINE.

| SYMBOL | DIMENSIONS | | | | NOTES |
|--------|-------------|-------|----------|------|-------|
| | MILLIMETERS | | INCHES | | |
| | MIN. | MAX. | MIN. | MAX. | |
| A | 4.06 | 4.83 | .160 | .190 | |
| A1 | 2.03 | 3.02 | .080 | .119 | |
| b | 0.51 | 0.99 | .020 | .039 | |
| b1 | 0.51 | 0.89 | .020 | .035 | 5 |
| b2 | 1.14 | 1.78 | .045 | .070 | |
| b3 | 1.14 | 1.73 | .045 | .068 | 5 |
| c | 0.38 | 0.74 | .015 | .029 | |
| c1 | 0.38 | 0.58 | .015 | .023 | 5 |
| c2 | 1.14 | 1.65 | .045 | .065 | |
| D | 8.38 | 9.65 | .330 | .380 | 3 |
| D1 | 6.86 | - | .270 | - | 4 |
| E | 9.65 | 10.67 | .380 | .420 | 3,4 |
| E1 | 6.22 | - | .245 | - | 4 |
| e | 2.54 BSC | | .100 BSC | | |
| L | 13.46 | 14.10 | .530 | .555 | |
| L1 | - | 1.65 | - | .065 | 4 |
| L2 | 3.56 | 3.71 | .140 | .146 | |

LEAD ASSIGNMENTS

- HEXFET**
- 1.- GATE
 - 2.- DRAIN
 - 3.- SOURCE
 - 4.- DRAIN

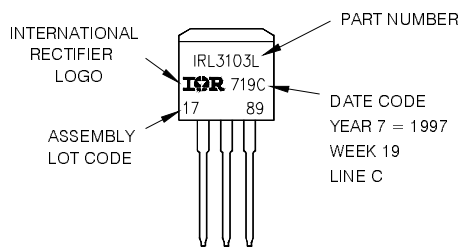
IGBTs, CoPACK

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER
- 4.- COLLECTOR

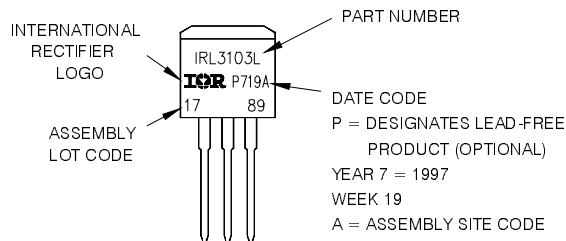
TO-262 Part Marking Information

EXAMPLE: THIS IS AN IRL3103L
LOT CODE 1789
ASSEMBLED ON WW 19, 1997
IN THE ASSEMBLY LINE 'C'

Note: "P" in assembly line position indicates "Lead - Free"



OR



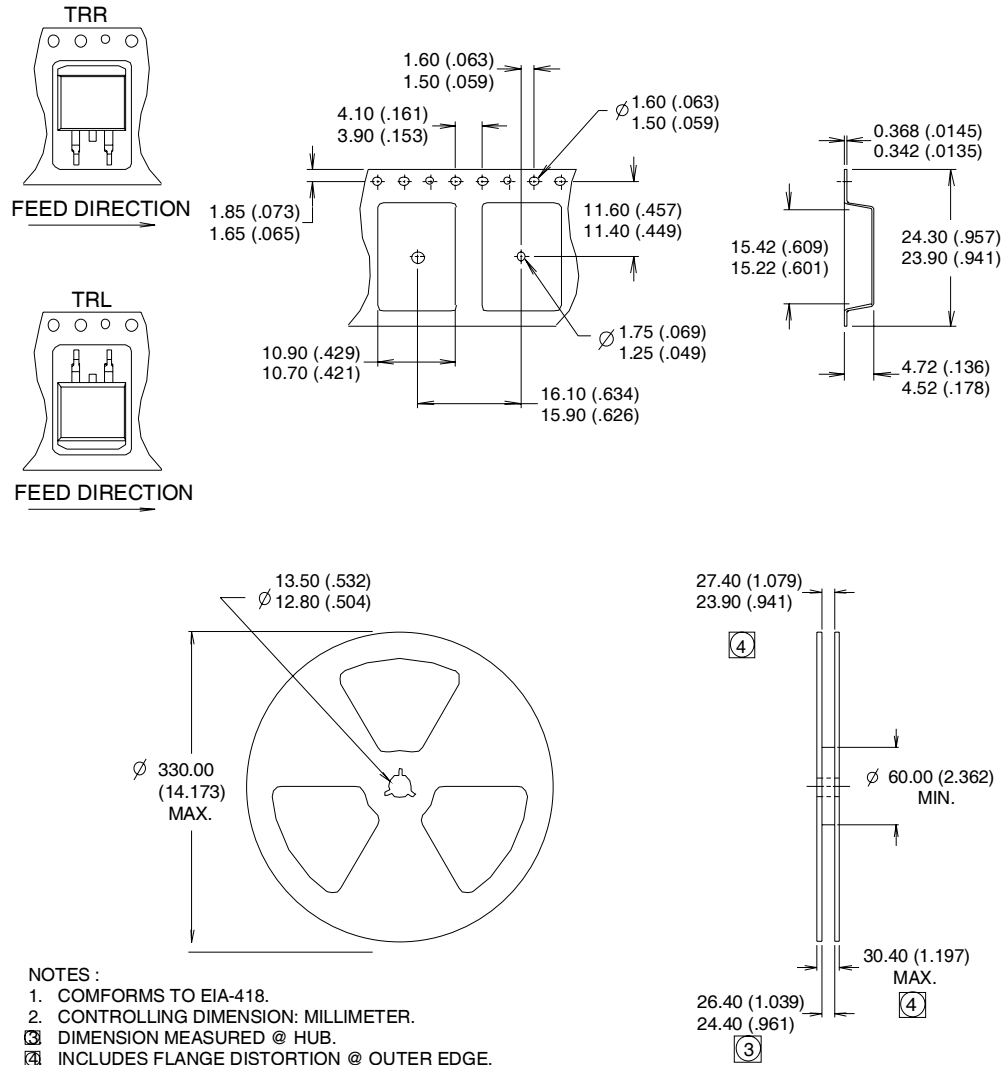
Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

IRF5210S/LPbF

International
IR Rectifier

D²Pak (TO-263AB) Tape & Reel Information

Dimensions are shown in millimeters (inches)



Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

Data and specifications subject to change without notice.
This product has been designed and qualified for the Industrial market.
Qualification Standards can be found on IR's Web site.

International
IR Rectifier

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105
TAC Fax: (310) 252-7903

Visit us at www.irf.com for sales contact information. 08/09

www.irf.com

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